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METHOD FOR THE FABRICATION OF CONTACTS IN AN INTEGRATED CIRCUIT DEVICE

ABSTRACT OF THE DISCLOSURE

The present invention provides a process for fabricating a contact plug in a semiconductor substrate having a contact opening formed therein that comprises depositing a barrier layer in the contact opening and on at least a portion of the semiconductor substrate, depositing a contact metal on the barrier layer within the contact opening, removing a substantial portion of the contact metal and the barrier layer from the semiconductor substrate and forming a contact plug within the contact opening, and subjecting the contact plug to a temperature sufficient to anneal the barrier layer.